

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
high concentration source and drain layers of a reverse conductive type formed in a semiconductor layer of one conductive type,
a gate electrode formed on a channel layer located between the source and drain layers,
a body layer of one conductive type in direct contact with the high concentration source layer, and
a low concentration drain layer of the reverse conductive type formed between the channel layer and the high concentration drain layer, wherein:
said body layer is formed only under said gate electrode.
2. (Previously Presented) A semiconductor device, according to claim 1, wherein the gate electrode is formed on the channel layer via a gate oxide film;
wherein the high concentration source layer is adjacent to one end of said gate electrode;
wherein the high concentration drain layer is formed apart from an other end of said gate electrode;
wherein the low concentration drain layer extends from under said gate electrode and surrounds said high concentration drain layer; and
wherein the body layer is formed between said high concentration source layer and said high concentration drain layer.
3. (Canceled)

4. (Previously Presented) A semiconductor device according to claim 1, wherein:
said low concentration drain layer is shallow under said gate electrode and deep under
said high concentration drain layer.

5. (Original) A semiconductor device, according to claim 1, wherein a reverse conductive
type layer is formed in a surface portion of the body layer.

6-21. (Cancelled).

22. (Currently Amended) A semiconductor device comprising:
high concentration source and drain layers of a reverse conductive type formed in a
semiconductor layer of one conductive type;
a gate electrode on a channel layer located between the high concentration source and
drain layers and formed via a gate oxide film;
a body layer of one conductive type formed only under the gate electrode and formed
apart from the high concentration source and drain layers; and
low concentration source and drain layers of the reverse conductive type respectively
surrounding said high concentration source layer and said high concentration drain layer;
wherein the low concentration source and drain layers are separated from each other by
the body layer; and
wherein the body layer is in direct contact with the low concentration source and drain
layers such that the body layer protrudes from the low concentration source and drain layers in a
downward direction.

23. (Previously Presented) The semiconductor device of claim 22 wherein said low
concentration source and drain layers are shallow under said gate electrode and deep under said
high concentration source and drain layers.

24. (New) The semiconductor device of claim 22 further comprising a gate oxide film above the body layer, wherein the body layer is in direct contact with the gate oxide film.

25. (New) The semiconductor device of claim 24 wherein the body layer has an approximately uniform width from the gate oxide film to a bottom surface of the body layer.

26. (New) A semiconductor device comprising:
high concentration source and drain layers of a reverse conductive type formed in a semiconductor layer of one conductive type;
a gate electrode on a channel layer located between the high concentration source and drain layers and formed via a gate oxide film;
a body layer of one conductive type formed only under the gate electrode and formed apart from the high concentration source and drain layers; and
low concentration source and drain layers of the reverse conductive type respectively surrounding said high concentration source layer and said high concentration drain layer;
wherein the low concentration source and drain layers are separated from each other by the body layer; and
wherein the body layer is in direct contact with the low concentration source and drain layers along portions of each side of the body layer, and the body layer extends in a downward direction to a position below bottom-most points of contact of the body layer with the low concentration source and drain layer.